

<b>Notice of References Cited</b>	Application/Control No. 10/812,141		Applicant(s)/Patent Under Reexamination BARRACK ET AL.	
	Examiner Thong H. Vu		Art Unit 2619	Page 1 of 1

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*	C	US-2004/0120349 A1	06-2004	Border et al.	370/474
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\*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)  
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.